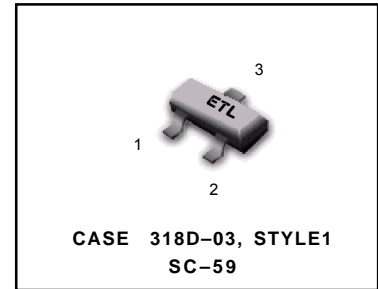
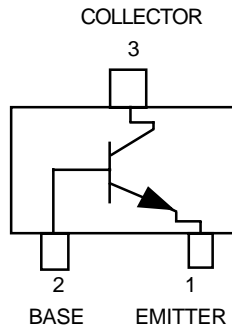


NPN RF Amplifier Transistors

Surface Mount

MSC2295-BT1
MSC2295-CT1



MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	30	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	20	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	5.0	Vdc
Collector Current - Continuous	I_C	30	mAdc

THERMAL CHARACTERISTICS

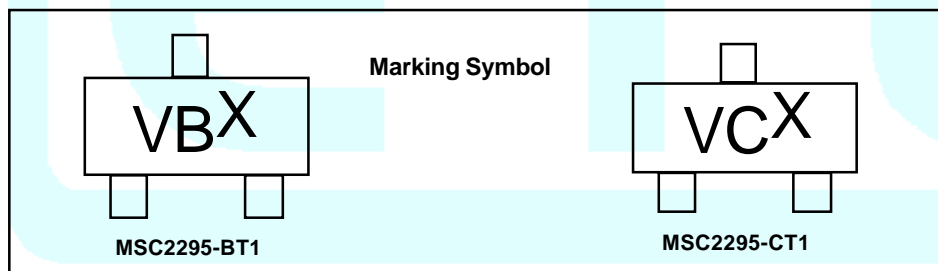
Characteristic	Symbol	Max	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Characteristic	Symbol	Min	Max	Unit
Collector-Base Cutoff Current ($V_{CB} = 10 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	0.1	μAdc
DC Current Gain ⁽¹⁾ ($V_{CB} = 10 \text{ Vdc}, I_C = -1.0 \text{ mAdc}$)	MSC2295-BT1 MSC2295-CT1	70 110	140 220	—
Collector-Gain - Bandwidth Product ($V_{CB} = 10 \text{ Vdc}, I_E = -1.0 \text{ mAdc}$)	f_T	150	—	MHz
Reverse Transistor Capacitance ($V_{CE} = 10 \text{ Vdc}, I_C = 1.0 \text{ mAdc}, f = 10.7 \text{ MHz}$)	C_{re}	—	1.5	pF

1. Pulse Test: Pulse Width $\leq 300 \text{ ms}$, D.C. $\leq 2\%$.

DEVICE MARKING



The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.